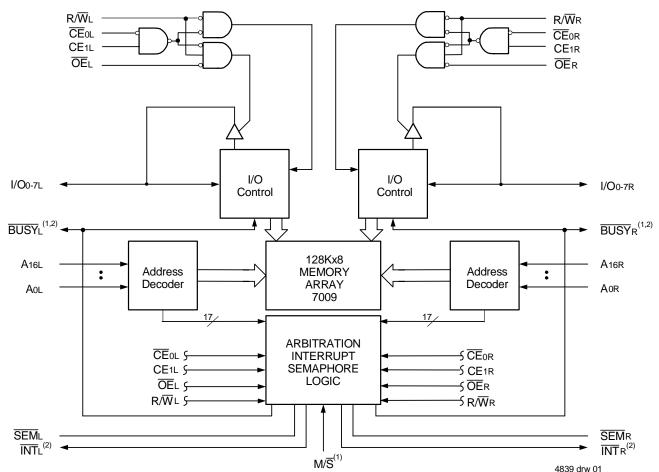
HIGH-SPEED 128K x 8 DUAL-PORT STATIC RAM

Features

- True Dual-Ported memory cells which allow simultaneous reads of the same memory location
- High-speed access
 - Commercial: 15/20ns (max.)
 - Industrial: 20ns (max.)
- Low-power operation
 - IDT7009L Active: 1W (typ.)
 - Standby: 1mW (typ.)
- Dual chip enables allow for depth expansion without external logic
- IDT7009 easily expands data bus width to 16 bits or more using the Master/Slave select when cascading more than one device

Functional Block Diagram

- M/S = VIH for BUSY output flag on Master, M/S = VIL for BUSY input on Slave
- Interrupt Flag
- On-chip port arbitration logic
- Full on-chip hardware support of semaphore signaling between ports
- Fully asynchronous operation from either port
- TTL-compatible, single 5V (±10%) power supply
- Available in a 100-pin TQFP
- Industrial temperature range (-40°C to +85°C) is available for selected speeds
- Green parts available, see ordering information



NOTES:

1. $\overline{\text{BUSY}}$ is an input as a Slave (M/S = VIL) and an output when it is a Master (M/S = VIH).

2. BUSY and INT are non-tri-state totem-pole outputs (push-pull).

7009L

High-Speed 128K x 8 Dual-Port Static RAM

Description

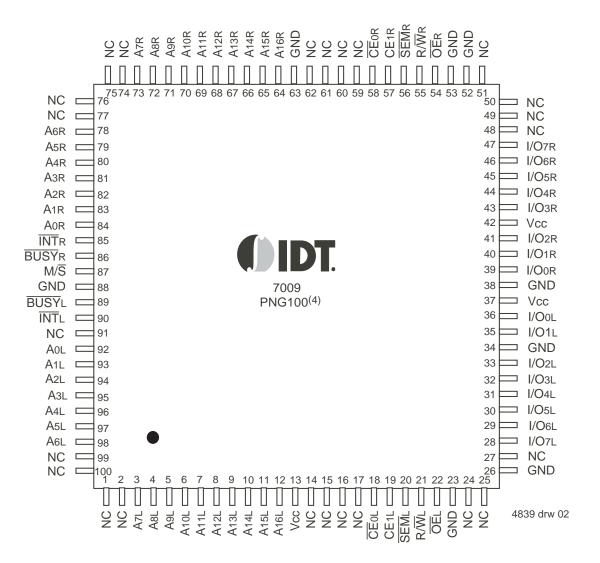
7009

The IDT7009 is a high-speed 128K x 8 Dual-Port Static RAM. The IDT7009 is designed to be used as a stand-alone 1024K-bit Dual-Port RAM or as a combination MASTER/SLAVE Dual-Port RAMfor 16-bit-ormore word systems. Using the IDT MASTER/SLAVE Dual-Port RAM approach in 16-bit or wider memory system applications results in fullspeed, error-free operation without the need for additional discrete logic. This device provides two independent ports with separate control, address, and I/O pins that permit independent, asynchronous access for reads or writes to any location in memory. An automatic power down feature controlled by the chip enables (CE0 and CE1) permit the on-chip circuitry of each port to enter a very low standby power mode.

Fabricated using a CMOS high-performance technology, these devices typically operate on only 1W of power.

The IDT7009 is packaged in a 100-pin Thin Quad Flatpack (TQFP).

Pin Configurations^(1,2,3)



- 1. All Vcc pins must be connected to power supply.
- 2. All GND pins must be connected to ground.
- 3. Package body is approximately 14mm x 14mm x 1.4mm.
- 4. This package code is used to reference the package diagram.

7009L High-Speed 128K x 8 Dual-Port Static RAM

Pin Names

Left Port	Right Port	Names
CEOL, CE1L	$\overline{\text{CE}}$ OR, CE1R	Chip Enables
R/WL	R/WR	Read/Write Enable
ŌĒL	ŌĒR	Output Enable
Aol - A16l	Aor - A16r	Address
1/Ool - 1/07l	I/O0r - I/O7r	Data Input/Output
SEML	SEM R	Semaphore Enable
ĪNTL	INT R	Interrupt Flag
BUSYL	BUSYR	Busy Flag
М	/S	Master or Slave Select
Vcc		Power
G	ND	Ground

4839 tbl 01

Absolute Maximum Ratings⁽¹⁾

Symbol	Rating	Commercial & Industrial	Military	Unit
Vterm ⁽²⁾	Terminal Voltage with Respect to GND	-0.5 to +7.0	-0.5 to +7.0	V
Tbias	Temperature Under Bias	-55 to +125	-65 to +135	۰C
Tstg	Storage Temperature	-65 to +150	-65 to +150	٥C
Ιουτ	DC Output Current	50	50	mA

NOTES:

- Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
- 2. VTERM must not exceed Vcc + 10% for more than 25% of the cycle time or 10ns maximum, and is limited to \leq 20mA for the period of VTERM \geq Vcc + 10%.

Maximum Operating Temperature and Supply Voltage

Grade	Ambient Temperature ⁽²⁾	GND	Vcc
Military	-55°C to +125°C	0V	5.0V <u>+</u> 10%
Commercial	0°C to +70°C	0V	5.0V <u>+</u> 10%
Industrial	-40°C to +85°C	0V	5.0V <u>+</u> 10%

NOTES:

1. This is the parameter TA. This is the "instant on" case temperature.

Industrial and Commercial Temperature Ranges

Recommended DC Operating Conditions

Symbol	Parameter	Min.	Тур.	Max.	Unit
Vcc	Supply Voltage	4.5	5.0	5.5	V
GND	Ground	0	0	0	V
Vн	Input High Voltage	2.2	-	6.0 ⁽²⁾	V
Vil	Input Low Voltage	-0.5 ⁽¹⁾		0.8	۷
					4839 tbl 04

NOTES:

1. $V_{IL} \ge -1.5V$ for pulse width less than 10ns.

2. VTERM must not exceed Vcc + 10%.

Capacitance

(TA = +	25°C,	f =	1.0MHz)	(TQFP	Only)
---------	-------	-----	---------	-------	-------

Symbol	Parameter ⁽¹⁾	Conditions ⁽²⁾	Max.	Unit
Cin	Input Capacitance	VIN = 3dV	9	рF
Соит	Output Capacitance	Vout = 3dV	10	pF
				4839 tbl 05

NOTES:

- This parameter is determined by device characterization but is not production tested.
- 3dV represents the interpolated capacitance when the input and output signals switch from 0V to 3V or from 3V to 0V.

4839 tbl 03

7009L High-Speed 128K x 8 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

4839 tbl 06

4839 tbl 08

Truth Table I: Chip Enable^(1,2)

Ē	CE ₀	CE1	Mode
	Vil	Vн	Port Selected (TTL Active)
L	<u><</u> 0.2V	<u>></u> Vcc -0.2V	Port Selected (CMOS Active)
	Vih	Х	Port Deselected (TTL Inactive)
	Х	Vil	Port Deselected (TTL Inactive)
Н	<u>></u> Vcc -0.2V	Х	Port Deselected (CMOS Inactive)
	Х	<u><</u> 0.2V	Port Deselected (CMOS Inactive)

NOTES:

1. Chip Enable references are shown above with the actual \overline{CE}_0 and CE_1 levels, \overline{CE} is a reference only.

2. $H' = V_{IH}$ and $L' = V_{IL}$.

3. CMOS standby requires 'X' to be either \leq 0.2V or \geq Vcc - 0.2V.

Truth Table II: Non-Contention Read/Write Control

	Inpu	uts ⁽¹⁾		Outputs	
CE ⁽²⁾	R/W	ŌĒ	SEM	I/O0-7	Mode
Н	Х	Х	Н	High-Z	Deselected: Power-Down
L	L	Х	Н	DATAIN	Write to memory
L	Н	L	Н	DATAOUT	Read memory
Х	Х	Н	Х	High-Z	Outputs Disabled
NOTEC				-	4839 drw 07

NOTES:

1. Aol – A16l \neq Aor – A16r.

2. Refer to Chip Enable Truth Table.

Truth Table III: Semaphore Read/Write Control⁽¹⁾

	Inp	uts		Outputs	
CE ⁽²⁾	R/W	ŌĒ	SEM	I/O0-7	Mode
Н	Н	L	L	DATAOUT	Read Semaphore Flag Data Out
Н	\uparrow	Х	L	DATAIN	Write I/Oo into Semaphore Flag
L	Х	Х	L		Not Allowed

NOTES:

1. There are eight semaphore flags written to via I/Oo and read from all the I/Os (I/Oo-I/O7). These eight semaphore flags are addressed by Ao-A2.

2. Refer to Chip Enable Truth Table.

7009L High-Speed 128K x 8 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽²⁾ ($Vcc = 5.0V \pm 10\%$)

			7009L		
Symbol	Parameter	Test Conditions		Мах.	Unit
Lu	Input Leakage Current ⁽¹⁾	Vcc = 5.5V, VIN = 0V to Vcc	-	5	μA
Ilo	Output Leakage Current	$\overline{CE} = V_{IH}$, Vout = 0V to Vcc	I	5	μA
Vol	Output Low Voltage	Iol = 4mA		0.4	V
Vон	Output High Voltage	IoH = -4mA	2.4		V

NOTES:

1. At Vcc \leq 2.0V, input leakages are undefined.

2. Refer to Chip Enable Truth Table.

7009L15 70091 20 Com'l Only Com'l & Ind Symbol Parameter **Test Condition** Version Typ.⁽¹⁾ Max Typ.⁽¹⁾ Max Unit $$\label{eq:cell} \begin{split} \overline{\underline{CE}} &= V_{IL}, \mbox{ Outputs Disabled } \\ \overline{SEM} &= V_{IH} \\ f &= f_{MAX}^{(2)} \end{split}$$ **I**CC Dynamic Operating COM'L 300 mΑ 220 340 200 L Current (Both Ports Active) IND L 200 360 mΑ **I**SB1 Standby Current COM'L L 65 100 50 75 (Both Ports - TTL Level IND Inputs) Т 50 120 _ **I**SB2 Standby Current $\overline{CE}^{"}A^{"} = VIL \text{ and } \overline{CE}^{"}B^{"} = VIH^{(4)}$ COM'L L 145 225 130 195 mΑ Active Port Outputs Disabled, $f=fMAX^{(2)}$, SEMR = SEML = VIH (One Port - TTL Level Inputs) IND 235 1 _ 130 Full Standby Current (Both Ports - All CMOS Level Inputs) Both Ports CEL and COM'L L 0.2 3.0 mΑ **I**SB3 0.2 3.0 $\overline{CER} \ge VCC - 0.2V$, VIN $\ge VCC - 0.2V$ <u>or VIN < 0.2V</u>, $f = 0^{(3)}$ IND L 0.2 6.0 $\overline{\text{SEM}}_{R} = \overline{\text{SEM}}_{L} \ge \text{VCC} - 0.2\text{V}$ $\begin{array}{l} \overline{\underline{CE}}^{*} \mathbb{A}^{*} &\leq 0.2V \text{ and} \\ \overline{\underline{CE}}^{*} \mathbb{B}^{*} &\geq \underline{Vcc} - 0.2V^{(4)}, \\ \overline{SEMR} &= \overline{SEML} \geq Vcc - 0.2V, \end{array}$ **I**SB4 Full Standby Current COM'L L 135 220 120 190 mΑ (One Port - All CMOS Level Inputs) IND L 120 $VIN \ge VCC - 0.2\overline{V}$ or $VIN \le 0.2V$, 230 Active Port Outputs Disabled, $f = f_{MAX}^{(2)}$

NOTES:

1. Vcc = 5V, TA = +25°C, and are not production tested. Icccc = 120mA (Typ.)

2. At f = fmax, address and control lines (except Output Enable) are cycling at the maximum frequency read cycle of 1/ trc, and using "AC Test Conditions" of input levels of GND to 3V.

3. f = 0 means no address or control lines change.

4. Port "A" may be either left or right port. Port "B" is the opposite from port "A".

5. Refer to Chip Enable Truth Table.

DC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range⁽¹⁾ ($Vcc = 5.0V \pm 10\%$)

4839 tbl 10

4839 tbl 09



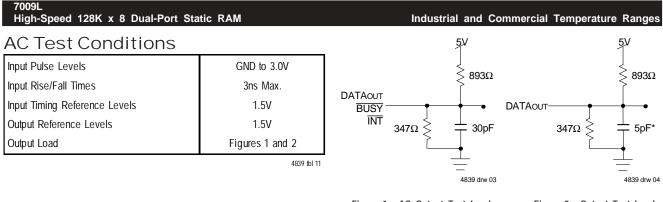
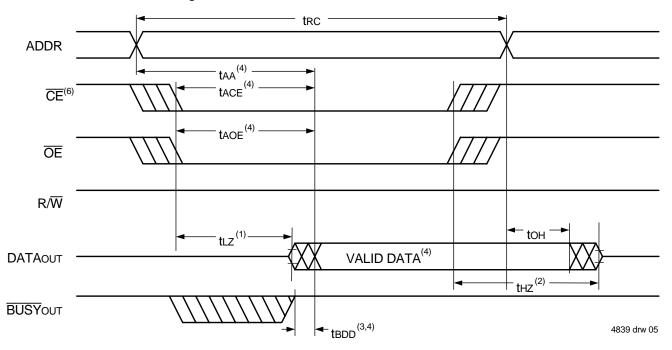


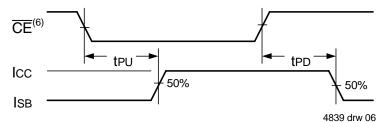
Figure 1. AC Output Test Load

Figure 2. Output Test Load (for tLz, tHz, twz, tow) * Including scope and jig.

Waveform of Read Cycles⁽⁵⁾



Timing of Power-Up Power-Down



- 1. Timing depends on which signal is asserted last, $\overline{\text{OE}}$ or $\overline{\text{CE}}$.
- 2. Timing depends on which signal is de-asserted first $\overline{\text{CE}}$ or $\overline{\text{OE}}.$
- 3. tbbb delay is required only in cases where the opposite port is completing a write operation to the same address location. For simultaneous read operations BUSY has no relation to valid output data.
- 4. Start of valid data depends on which timing becomes effective last tAOE, tACE, tAA or tBDD.
- 5. $\overline{\text{SEM}} = \text{VIH}.$
- 6. Refer to Chip Enable Truth Table.

7009L High-Speed 128K x 8 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

			7009L15 Com'l Only		7009L20 Com'l & Ind	
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
READ CYCLE			-			
trc	Read Cycle Time	15		20		ns
taa	Address Access Time	_	15		20	ns
tace	Chip Enable Access Time ⁽⁴⁾	_	15		20	ns
taoe	Output Enable Access Time	_	10		12	ns
tон	Output Hold from Address Change	3	_	3	_	ns
tLz	Output Low-Z Time ^(1,2)	3		3	_	ns
tHZ	Output High-Z Time ^(1,2)		10		10	ns
t₽U	Chip Enable to Power Up Time ⁽²⁾	0		0	_	ns
tPD	Chip Disable to Power Down Time ⁽²⁾		15		20	ns
tSOP	Semaphore Flag Update Pulse (OE or SEM)	10		10		ns
İ SAA	Semaphore Address Access Time		15		20	ns

4839 tbl 12

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage

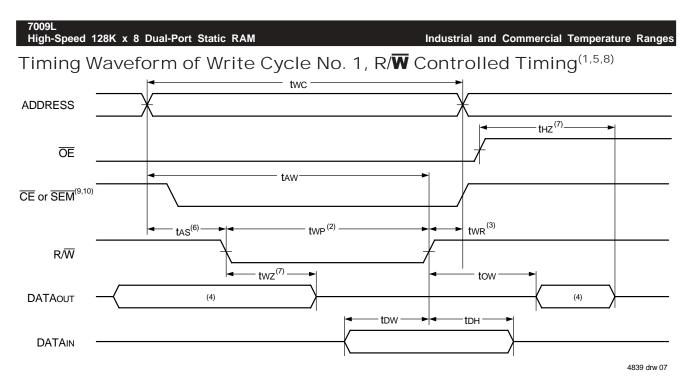
			9L15 I Only			
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
WRITE CYCL	E					
twc	Write Cycle Time	15		20	_	ns
tew	Chip Enable to End-of-Write ⁽³⁾	12		15	_	ns
taw	Address Valid to End-of-Write	12		15	_	ns
tas	Address Set-up Time ⁽³⁾	0		0	_	ns
twp	Write Pulse Width	12		15	_	ns
twr	Write Recovery Time	0		0	_	ns
tow	Data Valid to End-of-Write	10		15	_	ns
tHZ	Output High-Z Time ^(1,2)		10		10	ns
tон	Data Hold Time ⁽⁴⁾	0		0		ns
twz	Write Enable to Output in High-Z ^(1,2)		10		10	ns
tow	Output Active from End-of-Write ^(1,2,4)	0		0		ns
tswrd	SEM Flag Write to Read Time	5		5		ns
tsps	SEM Flag Contention Window	5		5		ns
NOTES:	·	-	-	-	-	4839 tbl 13

1. Transition is measured 0mV from Low or High-impedance voltage with Output Test Load (Figure 2).

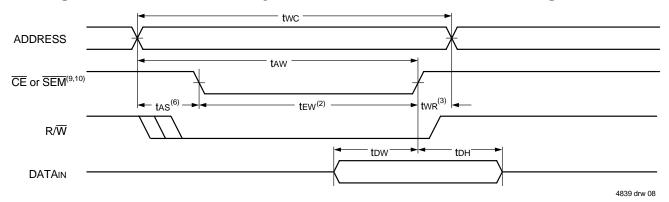
2. This parameter is guaranteed by device characterization, but is not production tested.

3. To access RAM, \overline{CE} = VIL and \overline{SEM} = VIH. To access semaphore, \overline{CE} = VIH and \overline{SEM} = VIL. Either condition must be valid for the entire tew time.

4. The specification for tDH must be met by the device supplying write data to the RAM under all operating conditions. Although tDH and tow values will vary over voltage and temperature, the actual tDH will always be smaller than the actual tow.



Timing Waveform of Write Cycle No. 2, CE Controlled Timing^(1,5)



NOTES:

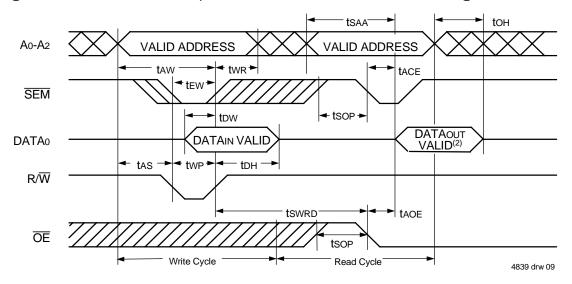
- 1. R/\overline{W} or $\overline{CE} = V_{IH}$ during all address transitions.
- 2. A write occurs during the overlap (tew or twp) of a \overline{CE} = VIL and a R/W = VIL for memory array writing cycle.
- 3. twr is measured from the earlier of CE or R/W (or SEM or R/W) going HIGH to the end of write cycle.
- 4. During this period, the I/O pins are in the output state and input signals must not be applied.
- 5. If the CE or SEM = VIL transition occurs simultaneously with or after the R/W = VIL transition, the outputs remain in the High-impedance state.
- 6. Timing depends on which enable signal is asserted last, \overline{CE} or R/\overline{W} .
- 7. This parameter is guaranteed by device characterization, but is not production tested. Transition is measured 0mV from steady state with the Output Test Load (Figure 2).
- 8. If $\overline{OE} = V_{IL}$ during R/W controlled write cycle, the write pulse width must be the larger of twp or (twz + tow) to allow the I/O drivers to turn off and data to be placed on the bus for the required tow. If $\overline{OE} = V_{IH}$ during an R/W controlled write cycle, this requirement does not apply and the write pulse can be as short as the specified twp.
- 9. To access RAM, CE = VIL and SEM = VIH. To access semaphore, CE = VIH and SEM = VIL. tew must be met for either condition.

10. Refer to Chip Enable Truth Table.

7009L High-Speed 128K x 8 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

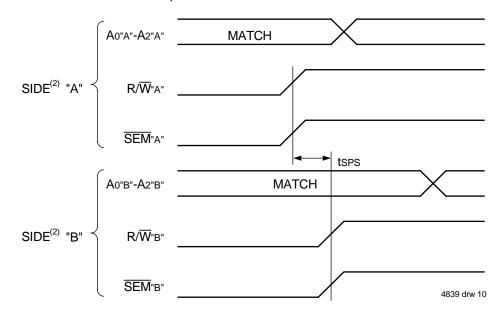
Timing Waveform of Semaphore Read after Write Timing, Either Side⁽¹⁾



NOTES:

- 1. $\overline{CE} = V_{IH}$ for the duration of the above timing (both write and read cycle) (Refer to Chip Enable Truth Table).
- 2. "DATAOUT VALID" represents all I/O's (I/Oo I/O7) equal to the semaphore value.

Timing Waveform of Semaphore Write Contention^(1,3,4)



- 1. DOR = DOL = VIL, $\overline{CE}L = \overline{CE}R = VIH$ (Refer to Chip Enable Truth Table).
- 2. All timing is the same for left and right ports. Port "A" may be either left or right port. "B" is the opposite from port "A".
- 3. This parameter is measured from R/W"A" or SEM"A" going HIGH to R/W"B" or SEM"B" going HIGH.
- 4. If tsps is not satisfied, the semaphore will fall positively to one side or the other, but there is no guarantee which side will obtain the flag.

7009L High-Speed 128K x 8 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

		7009L15 Com'l Only		7009L20 Com'l & Ind		
Symbol	Parameter	Min.	Max.	Min.	Max.	Unit
BUSY TIMING	і (М/S=Vін)					
tbaa	BUSY Access Time from Address Match		15		20	ns
tbda	BUSY Disable Time from Address Not Matched		15		20	ns
tBAC	BUSY Access Time from Chip Enable Low		15		20	ns
tBDC	BUSY Access Time from Chip Enable High	—	15		17	ns
taps	Arbitration Priority Set-up Time ⁽²⁾	5		5		ns
tbdd	BUSY Disable to Valid Data ⁽³⁾		15		17	ns
twн	Write Hold After BUSY ⁽⁵⁾	12		15		ns
BUSY TIMING	(M/S=VIL)					
twв	BUSY Input to Write ⁽⁴⁾	0		0	_	ns
twн	Write Hold After BUSY ⁽⁵⁾	12		15		ns
PORT-TO-POF	RT DELAY TIMING					
twdd	Write Pulse to Data Delay ⁽¹⁾		30		45	ns
tddd	Write Data Valid to Read Data Delay ⁽¹⁾		25		30	ns
	·	-	-	•	•	4839 tbl 14

NOTES:

1. Port-to-port delay through RAM cells from writing port to reading port, refer to "Timing Waveform of Write with Port-to-Port Read and BUSY (M/S = VI-)".

2. To ensure that the earlier of the two ports wins.

3. tBDD is a calculated parameter and is the greater of 0, twDD - twp (actual) or tDDD - tDw (actual).

4. To ensure that the write cycle is inhibited on port "B" during contention on port "A".

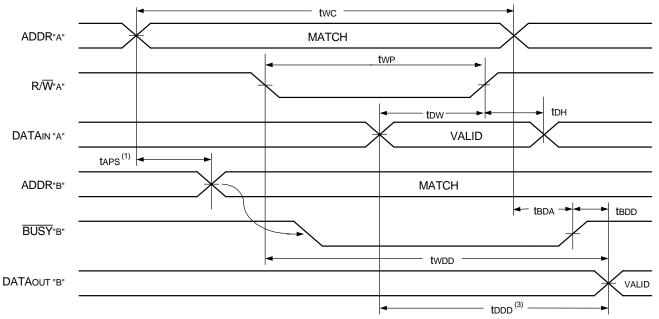
5. To ensure that a write cycle is completed on port "B" after contention on port "A".

7009L High-Speed 128K x 8 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

4839 drw 11

Timing Waveform of Write with Port-to-Port Read and $\overline{\text{BUSY}}$ (M/ $\overline{\text{S}}$ = VIH)^(2,4,5)



NOTES:

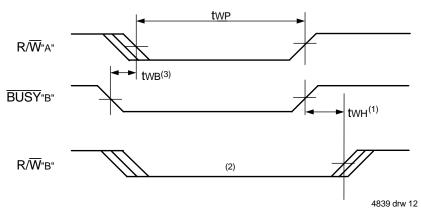
1. To ensure that the earlier of the two ports wins. taps is ignored for $M/\overline{S} = V_{IL}$ (SLAVE).

- 2. $\overline{CE}_{L} = \overline{CE}_{R} = V_{IL}$, refer to Chip Enable Truth Table.
- 3. $\overline{OE} = V_{IL}$ for the reading port.

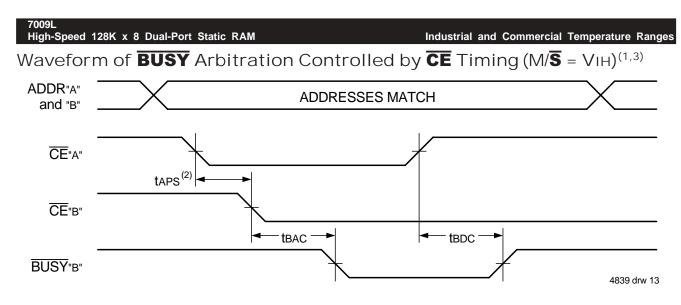
4. If M/S = VIL (SLAVE), BUSY is an input. Then for this example BUSY "A" = VIH and BUSY "B" input is shown above.

5. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

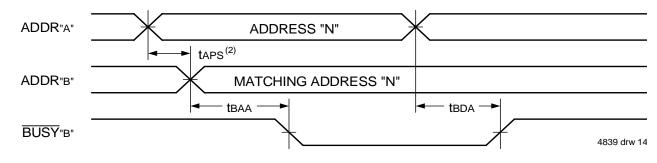
Timing Waveform of Write with $\overline{\text{BUSY}}$ (M/ $\overline{\text{S}}$ = VIL)



- 1. twH must be met for both BUSY input (SLAVE) and output (MASTER).
- 2. BUSY is asserted on port "B" blocking R/W"B", until BUSY"B" goes HIGH.
- 3. twb is only for the 'Slave' version.



Waveform of **BUSY** Arbitration Cycle Controlled by Address Match Timing $(M/S = VIH)^{(1)}$



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. If tAPS is not satisfied, the BUSY signal will be asserted on one side or another but there is no guarantee on which side BUSY will be asserted.

3. Refer to Chip Enable Truth Table.

AC Electrical Characteristics Over the Operating Temperature and Supply Voltage Range

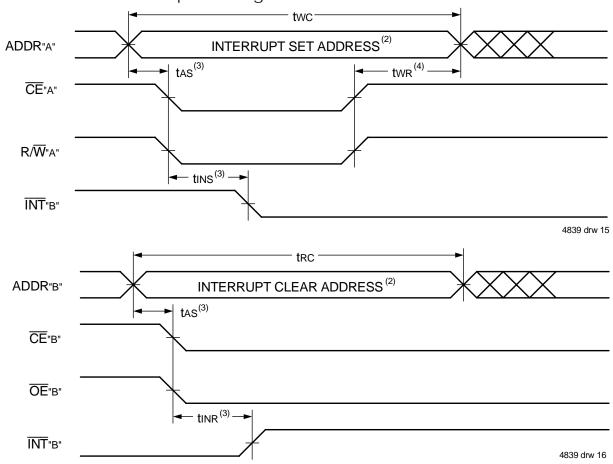
		7009L15 7009L20 Com'l Only Com'l & Ind				
Symbol	Parameter	Min.	Мах.	Min.	Max.	Unit
INTERRUPT T	IMING					
tas	Address Set-up Time	0	_	0		ns
twr	Write Recovery Time	0	-	0		ns
tins	Interrupt Set Time	-	15		20	ns
tinr	Interrupt Reset Time		15		20	ns

4839 tbl 15

7009L High-Speed 128K x 8 Dual-Port Static RAM

Industrial and Commercial Temperature Ranges

Waveform of Interrupt Timing^(1,5)



NOTES:

1. All timing is the same for left and right ports. Port "A" may be either the left or right port. Port "B" is the port opposite from port "A".

2. See Interrupt Truth Table.

3. Timing depends on which enable signal (\overline{CE} or R/\overline{W}) is asserted last.

4. Timing depends on which enable signal ($\overline{\text{CE}}$ or R/W) is de-asserted first.

5. Refer to Chip Enable Truth Table.

Truth Table IV — Interrupt Flag^(1,4,5)

Left Port					Right Port					
R/₩L	CEL		A16L-A0L	ĨNT∟	R/WR		OER	A16R-A0R	Ī NT R	Function
L	L	Х	1FFFF	Х	Х	Х	Х	Х	L ⁽²⁾	Set Right INTR Flag
Х	Х	Х	Х	Х	Х	L	L	1FFFF	H ⁽³⁾	Reset Right INTR Flag
Х	Х	Х	Х	L ⁽³⁾	L	L	Х	1FFFE	Х	Set Left INTL Flag
Х	L	L	1FFFE	H ⁽²⁾	Х	Х	Х	Х	Х	Reset Left INTL Flag

NOTES:

1. Assumes $\overline{\text{BUSY}}_{L} = \overline{\text{BUSY}}_{R} = VIH$.

2. If $\overline{\text{BUSY}}L = VIL$, then no change.

3. If $\overline{\text{BUSY}}_{R} = V_{IL}$, then no change.

4. \overline{INT}_L and \overline{INT}_R must be initialized at power-up.

5. Refer to Chip Enable Truth Table.

7009L High-Speed 128K x 8 Dual-Port Static RAM

Truth Table V — Address **BUSY** Arbitration⁽⁴⁾

	In	puts	Out		
CEL	CER	Aol-A16l Aor-A16r	BUSYL ⁽¹⁾	BUSY R ⁽¹⁾	Function
Х	Х	NO MATCH	Н	Н	Normal
Н	Х	MATCH	Н	Н	Normal
Х	Н	MATCH	Н	Н	Normal
L	L	MATCH	(2)	(2)	Write Inhibit ⁽³⁾

NOTES:

4839 tbl 17

1. Pins BUSYL and BUSYR are both outputs when the part is configured as a master. Both are inputs when configured as a slave. BUSY outputs on the IDT7009 are push-pull, not open drain outputs. On slaves the BUSY input internally inhibits writes.

 "L" if the inputs to the opposite port were stable prior to the address and enable inputs of this port. "H" if the inputs to the opposite port became stable after the address and enable inputs of this port. If tAPS is not met, either BUSYL or BUSYR = LOW will result. BUSYL and BUSYR outputs can not be LOW simultaneously.

3. Writes to the left port are internally ignored when BUSYL outputs are driving LOW regardless of actual logic level on the pin. Writes to the right port are internally ignored when BUSYR outputs are driving LOW regardless of actual logic level on the pin.

4. Refer to Chip Enable Truth Table

Truth Table VI — Example of Semaphore Procurement Sequence^(1,2,3)

Functions	Do - D7 Left	Do - D7 Right	Status
No Action	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Right Port Writes "0" to Semaphore	0	1	No change. Right side has no write access to semaphore
Left Port Writes "1" to Semaphore	1	0	Right port obtains semaphore token
Left Port Writes "0" to Semaphore	1	0	No change. Left port has no write access to semaphore
Right Port Writes "1" to Semaphore	0	1	Left port obtains semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free
Right Port Writes "0" to Semaphore	1	0	Right port has semaphore token
Right Port Writes "1" to Semaphore	1	1	Semaphore free
Left Port Writes "0" to Semaphore	0	1	Left port has semaphore token
Left Port Writes "1" to Semaphore	1	1	Semaphore free

NOTES:

1. This table denotes a sequence of events for only one of the eight semaphores on the IDT7009.

2. There are eight semaphore flags written to via I/Oo and read from all I/O's (I/Oo-I/O7). These eight semaphores are addressed by Ao-A2.

3. $\overline{CE} = V_{IH}$, $\overline{SEM} = V_{IL}$ to access the semaphores. Refer to the Semaphore Read/Write Control Truth Table.

Functional Description

The IDT7009 provides two ports with separate control, address and I/O pins that permit independent access for reads or writes to any location in memory. The IDT7009 has an automatic power down feature controlled by \overline{CE} . The \overline{CE} and CE1 control the on-chip power down circuitry that permits the respective port to go into a standby mode when not selected ($\overline{CE} = VIH$). When a port is enabled, access to the entire memory array is permitted.

Interrupts

If the user chooses the interrupt function, a memory location (mail box or message center) is assigned to each port. The left port interrupt flag (\overline{INTL}) is asserted when the right port writes to memory location 1FFFE (HEX), where a write is defined as $\overline{CER} = R/\overline{WR} = VIL$ per Truth Table IV. The left port clears the interrupt through access of address location 1FFFE when $\overline{CEL} = \overline{OEL} = VIL$, R/\overline{W} is a "don't care". Likewise, the right port interrupt flag (\overline{INTR}) is asserted when the left port writes to memory location 1FFFF (HEX) and to clear the interrupt flag (\overline{INTR}), the right port must read the memory location 1FFFF. The message (8 bits) at 1FFFE or 1FFFF is user-defined since it is an addressable SRAM location. If the interrupt function is not used, address locations 1FFFE and 1FFFF are not used as mail boxes, but as part of the random access memory. Refer to Table IV for the interrupt operation.

4839 tbl 18

Industrial and Commercial Temperature Ranges

7009L High-Speed 128K x 8 Dual-Port Static RAM

BusyLogic

Busy Logic provides a hardware indication that both ports of the RAM have accessed the same location at the same time. It also allows one of the two accesses to proceed and signals the other side that the RAM is "busy". The $\overline{\text{BUSY}}$ pin can then be used to stall the access until the operation on the other side is completed. If a write operation has been attempted from the side that receives a $\overline{\text{BUSY}}$ indication, the write signal is gated internally to prevent the write from proceeding.

The use of BUSY logic is not required or desirable for all applications. In some cases it may be useful to logically OR the BUSY outputs together and use any BUSY indication as an interrupt source to flag the event of an illegal or illogical operation. If the write inhibit function of BUSY logic is not desirable, the BUSY logic can be disabled by placing the part in slave mode with the M/S pin. Once in slave mode the BUSY pin operates solely as a write inhibit input pin. Normal operation can be programmed by tying the BUSY pins HIGH. If desired, unintended write operations can be prevented to a port by tying the BUSY pin for that port LOW.

The BUSY outputs on the IDT7009 RAM in master mode, are pushpull type outputs and do not require pull up resistors to operate. If these RAMs are being expanded in depth, then the BUSY indication for the resulting array requires the use of an external AND gate.

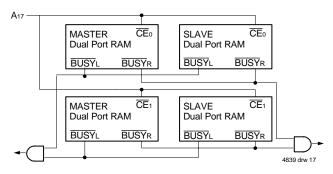


Figure 3. Busy and chip enable routing for both width and depth expansion with IDT7009 RAMs.

Width Expansion Busy Logic Master/Slave Arrays

When expanding an IDT7009 RAM array in width while using \overline{BUSY} logic, one master part is used to decide which side of the RAMs array will receive a \overline{BUSY} indication, and to output that indication. Any number of slaves to be addressed in the same address range as the master, use the \overline{BUSY} signal as a write inhibit signal. Thus on the IDT7009 RAM the \overline{BUSY} pin is an output if the part is used as a master (M/ \overline{S} pin = VIL) as shown in Figure 3.

If two or more master parts were used when expanding in width, a split decision could result with one master indicating BUSY on one side of the array and another master indicating BUSY on one other side of the array. This would inhibit the write operations from one port for part of a word and inhibit the write operations from the other port for the other part of the word.

The BUSY arbitration, on a master, is based on the chip enable and address signals only. It ignores whether an access is a read or write. In a master/slave array, both address and chip enable must be valid long enough for a BUSY flag to be output from the master before the actual write pulse can be initiated with the R/W signal. Failure to observe this timing

can result in a glitched internal write inhibit signal and corrupted data in the slave.

Semaphores

The IDT7009 is an extremely fast Dual-Port 128K x 8 CMOS Static RAM with an additional 8 address locations dedicated to binary semaphore flags. These flags allow either processor on the left or right side of the Dual-Port RAM to claim a privilege over the other processor for functions defined by the system designer's software. As an example, the semaphore can be used by one processor to inhibit the other from accessing a portion of the Dual-Port RAM or any other shared resource.

The Dual-Port RAM features a fast access time, and both ports are completely independent of each other. This means that the activity on the left port in no way slows the access time of the right port. Both ports are identical infunction to standard CMOS Static RAM and can be read from, orwritten to, at the same time with the only possible conflict arising from the simultaneous writing of, or a simultaneous READ/WRITE of, a non-semaphore location. Semaphores are protected against such ambiguous situations and may be used by the system program to avoid any conflicts in the non-semaphore portion of the Dual-Port RAM. These devices have an automatic power-down feature controlled by \overline{CE} , the Dual-Port RAM enable, and \overline{SEM} , the semaphore enable. The \overline{CE} and \overline{SEM} pins control on-chip power down circuitry that permits the respective port to go into standby mode when not selected. This is the condition which is shown in Truth Table II where \overline{CE} and \overline{SEM} are both HIGH.

Systems which can best use the IDT7009 contain multiple processors or controllers and are typically very high-speed systems which are software controlled or software intensive. These systems can benefit from a performance increase offered by the IDT7009s hardware semaphores, which provide a lockout mechanism without requiring complex programming.

Software handshaking between processors offers the maximum in system flexibility by permitting shared resources to be allocated in varying configurations. The IDT7009 does not use its semaphore flags to control any resources through hardware, thus allowing the system designer total flexibility in system architecture.

An advantage of using semaphores rather than the more common methods of hardware arbitration is that wait states are never incurred in either processor. This can prove to be a major advantage in very highspeed systems.

How the Semaphore Flags Work

The semaphore logic is a set of eight latches which are independent of the Dual-Port RAM. These latches can be used to pass a flag, or token, from one port to the other to indicate that a shared resource is in use. The semaphores provide a hardware assist for a use assignment method called "Token Passing Allocation." In this method, the state of a semaphore latch is used as a token indicating that shared resource is in use. If the left processor wants to use this resource, it requests the token by setting the latch. This processor then verifies its success in setting the latch by reading it. If it was successful, it proceeds to assume control over the shared resource. If it was not successful in setting the latch, it determines that the right side processor has set the latch first, has the token and is using the shared resource. The left processor can then either repeatedly request that semaphore's status or remove its request for that semaphore to perform

7009L

High-Speed 128K x 8 Dual-Port Static RAM

another task and occasionally attempt again to gain control of the token via the set and test sequence. Once the right side has relinquished the token, the left side should succeed in gaining control.

The semaphore flags are active LOW. A token is requested by writing a zero into a semaphore latch and is released when the same side writes a one to that latch.

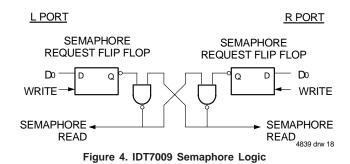
The eight semaphore flags reside within the IDT7009 in a separate memory space from the Dual-Port RAM. This address space is accessed by placing a LOW input on the \overline{SEM} pin (which acts as a chip select for the semaphore flags) and using the other control pins (Address, \overline{CE} , and R/\overline{W}) as they would be used in accessing a standard Static RAM. Each of the flags has a unique address which can be accessed by either side through address pins A0–A2. When accessing the semaphores, none of the other address pins has any effect.

When writing to a semaphore, only data pin Do is used. If a LOW level is written into an unused semaphore location, that flag will be set to a zero on that side and a one on the other side (see Table VI). That semaphore can now only be modified by the side showing the zero. When a one is written into the same location from the same side, the flag will be set to a one for both sides (unless a semaphore request from the other side is pending) and then can be written to by both sides. The fact that the side which is able to write a zero into a semaphore flags useful in interprocessor communications. (A thorough discussion on the use of this feature follows shortly.) A zero written into the same location from the other side will be stored in the semaphore request latch for that side until the semaphore is freed by the first side.

When a semaphore flag is read, its value is spread into all data bits so that a flag that is a one reads as a one in all data bits and a flag containing a zero reads as all zeros. The read value is latched into one side's output register when that side's semaphore select (SEM) and output enable (\overline{OE}) signals go active. This serves to disallow the semaphore from changing state in the middle of a read cycle due to a write cycle from the other side. Because of this latch, a repeated read of a semaphore in a test loop must cause either signal (SEM or \overline{OE}) to go inactive or the output will never change.

A sequence WRITE/READ must be used by the semaphore in order to guarantee that no system level contention will occur. A processor requests access to shared resources by attempting to write a zero into a semaphore location. If the semaphore is already in use, the semaphore request latch will contain a zero, yet the semaphore flag will appear as one, a fact which the processor will verify by the subsequent read (see Table VI). As an example, assume a processor writes a zero to the left port at a free semaphore location. On a subsequent read, the processor will verify that it has written successfully to that location and will assume control over the resource in question. Meanwhile, if a processor on the right side attempts to write a zero to the same semaphore flag it will fail, as will be verified by the fact that a one will be read from that semaphore on the right side during subsequent read. Had a sequence of READ/WRITE been used instead, system contention problems could have occurred during the gap between the read and write cycles.

It is important to note that a failed semaphore request must be followed by either repeated reads or by writing a one into the same location. The reason for this is easily understood by looking at the simple logic diagram of the semaphore flag in Figure 4. Two semaphore request latches feed into a semaphore flag. Whichever latch is first to present a zero to the semaphore flag will force its side of the semaphore flag LOW and the other side HIGH. This condition will continue until a one is written to the same semaphore request latch. Should the other side's semaphore request latch have been written to a zero in the meantime, the semaphore flag will flip



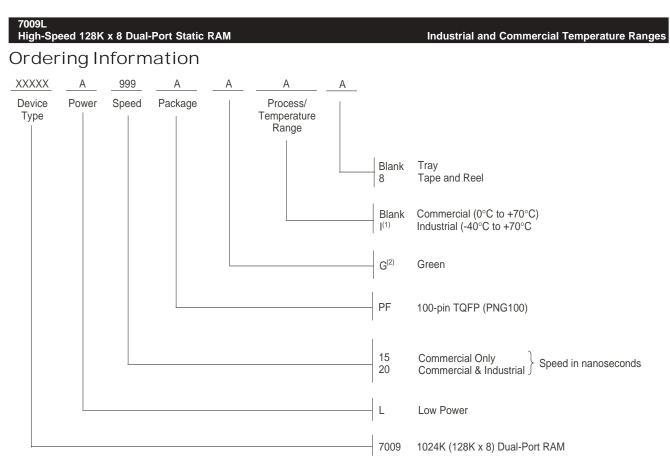
over to the other side as soon as a one is written into the first side's request latch. The second side's flag will now stay LOW until its semaphore request latch is written to a one. From this it is easy to understand that, if a semaphore is requested and the processor which requested it no longer needs the resource, the entire system can hang up until a one is written into that semaphore request latch.

The critical case of semaphore timing is when both sides request a single token by attempting to write a zero into it at the same time. The semaphore logic is specially designed to resolve this problem. If simultaneous requests are made, the logic guarantees that only one side receives the token. If one side is earlier than the other in making the request, the first side to make the request will receive the token. If both requests arrive at the same time, the assignment will be arbitrarily made to one port or the other.

One caution that should be noted when using semaphores is that semaphores alone do not guarantee that access to a resource is secure. As with any powerful programming technique, if semaphores are misused or misinterpreted, a software error can easily happen.

Initialization of the semaphores is not automatic and must be handled via the initialization program at power-up. Since any semaphore request flag which contains a zero must be reset to a one, all semaphores on both sides should have a one written into them at initialization from both sides to assure that they will be free when needed.

Industrial and Commercial Temperature Ranges



4839 drw 19

NOTE:

1. Contact your local sales office for industrial temp range for other speeds, packages and powers.

2. Green parts available. For specific speeds, packages and powers contact your local sales office. LEAD FINISH (SnPb) parts are Obsolete. Product Discontinuation Notice - PDN# SP-17-02

Orderable Part Information						
Speed (ns)	Orderable Part ID Pkg. Code		Pkg. Type	Temp. Grade		
15	7009L15PFG	PNG100	TQFP	С		
	7009L15PFG8	PNG100	TQFP	С		
20	7009L20PFG	PNG100	TQFP	С		
	7009L20PFG8	PNG100	TQFP	С		
	7009L20PFGI	PNG100	TQFP	I		
	7009L20PFGI8	PNG100	TQFP	I		

Datasheet Document History

09/30/99:		Initial Public Release
11/10/99:		Replaced IDT logo
01/05/01:	Page 3	Increased storage temperature parameter
		Clarified TA parameter
	Page 5	DC Electrical parameters-changed wording from "open" to "disabled"
	Page 14	Added IV to Truth Table in Interrupts paragraph
		Changed ±200mV to 0mV in notes
		Removed Preliminary specification
01/24/02:	Page 2	Added date revision for pin configuration
	Pages 3, 5, 7, 10 & 12	Removed Industrial temp footnote from all tables
	Pages 5, 7, 10 & 12	Added Industrial temp for 20ns speed to DC and AC Electrical Characteristics
	Page 17	Added Industrial temp offering to 20ns ordering information
	Pages 1 & 17	Replaced тм logo with ® logo
01/31/06:	Page 1	Added green availability to features
	Page 17	Added green indicator to ordering information
11/11/08:	Page 17	Removed "IDT" from orderable part number
08/04/14:	Page 17	Added Tape and Reel to Ordering Information
	Page 2 & 17	The package code PN100-1 changed to PN100 to match the standard package code
08/19/16:	Page 2	Changed diagram for the PN100 pin configuration by rotating package pin labels and pin
		numbers 90 degrees counter clockwise to reflect pin 1 orientation and added pin 1 dot at pin 1
		Added the IDT logo to the PN100 pin configurations and changed the text to be in
		alignment with new diagram marking specs and removed the date revision indicator
		Removed the Index and arrow indicators from the PN100 pin configuration
		Updated footnote references for PN100 pin configuration
10/10/17:		Product Discontinuation Notice - PDN# SP-17-02
		Last time buy expires June 15, 2018
05/06/19:	Page 2	Changed package code from PN100 to PNG100 in pin configuration
	Page 17	Revised LEAD FINISH note to indicate Obsolete
	5	Added Orderable Part Information
		In Ordering Information updated Tube or Tray to Tray
		Updated package code from PN100 to PNG100

IMPORTANT NOTICE AND DISCLAIMER

RENESAS ELECTRONICS CORPORATION AND ITS SUBSIDIARIES ("RENESAS") PROVIDES TECHNICAL SPECIFICATIONS AND RELIABILITY DATA (INCLUDING DATASHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES "AS IS" AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS OR IMPLIED, INCLUDING, WITHOUT LIMITATION, ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE, OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for developers skilled in the art designing with Renesas products. You are solely responsible for (1) selecting the appropriate products for your application, (2) designing, validating, and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, or other requirements. These resources are subject to change without notice. Renesas grants you permission to use these resources only for development of an application that uses Renesas products. Other reproduction or use of these resources is strictly prohibited. No license is granted to any other Renesas intellectual property or to any third party intellectual property. Renesas disclaims responsibility for, and you will fully indemnify Renesas and its representatives against, any claims, damages, costs, losses, or liabilities arising out of your use of these resources. Renesas' products are provided only subject to Renesas' Terms and Conditions of Sale or other applicable terms agreed to in writing. No use of any Renesas resources expands or otherwise alters any applicable warranties or warranty disclaimers for these products.

(Rev.1.0 Mar 2020)

Corporate Headquarters

TOYOSU FORESIA, 3-2-24 Toyosu, Koto-ku, Tokyo 135-0061, Japan www.renesas.com

Trademarks

Renesas and the Renesas logo are trademarks of Renesas Electronics Corporation. All trademarks and registered trademarks are the property of their respective owners.

Contact Information

For further information on a product, technology, the most up-to-date version of a document, or your nearest sales office, please visit: www.renesas.com/contact/

X-ON Electronics

Largest Supplier of Electrical and Electronic Components

Click to view similar products for SRAM category:

Click to view products by Renesas manufacturer:

Other Similar products are found below :

CY6116A-35DMB CY7C1049GN-10VXI GS8161Z36DD-200I GS88237CB-200I RMLV0408EGSB-4S2#AA0 IDT70V5388S166BG IS64WV3216BLL-15CTLA3 IS66WVE4M16ECLL-70BLI PCF8570P K6F2008V2E-LF70000 K6T4008C1B-GB70 CY7C1353S-100AXC AS6C8016-55BIN AS7C164A-15PCN 515712X IDT71V67603S133BG IS62WV51216EBLL-45BLI IS63WV1288DBLL-10HLI IS66WVE2M16ECLL-70BLI IS66WVE4M16EALL-70BLI IS61WV102416DBLL-10TLI CY7C1381KV33-100AXC CY7C1381KVE33-133AXI 8602501XA 5962-3829425MUA 5962-3829430MUA 5962-8866201YA 5962-8866204TA 5962-9062007MXA 5962-9161705MXA GS882Z18CD-150I 8413202RA 5962-8866208YA 5962-8866203YA IS61WV102416DBLL-10BLI IS66WVC2M16ECLL-7010BLI CY7C1380KV33-250AXC AS6C8016-55BINTR GS81284Z18B-250I AS7C34096B-10TIN GS84018CB-200I IS62WV25616EALL-55TLI IS61WV204816BLL-10TLI GS8128418B-167IV CY7C1460KV25-200BZXI CY7C1315KV18-333BZXC CY62157G30-45ZSXI 71V016SA12YG RMLV0416EGBG-4S2#AC0 CY62126EV18LL-70BVXI